

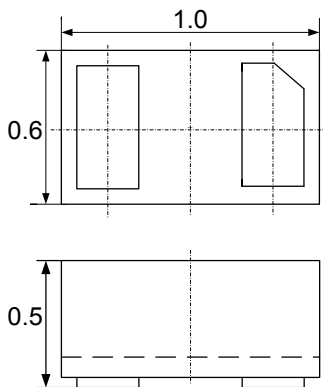
Description

The AU1501P1 is a uni-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The AU1501P1 complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free DFN package. The small size and high ESD surge protection make AU1501P1 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

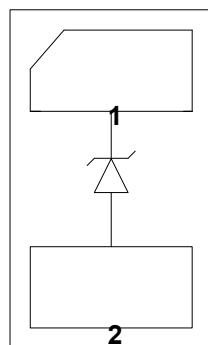
Features

- Ultra small package: 1.0x0.6x0.5mm
- Protects one data or power line
- Ultra low leakage: nA level
- Operating voltage: 15V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 10A (8/20 μs)
- RoHS Compliant

Dimensions and Pin Configuration



Package Dimensions



Circuit and Pin Schematic

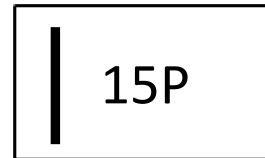
Mechanical Characteristics

- Package: DFN1006-2 (1.0x0.6x0.5mm)
- Case Material: “Green” Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Power Supply
- Keypads, Side Keys, LCD Displays

Marking Information



15P: Device Marking Code
 Bar denotes cathode

Ordering Information

Part Number	Packaging	Reel Size
AU1501P1	10000/Tape & Reel	7 inch

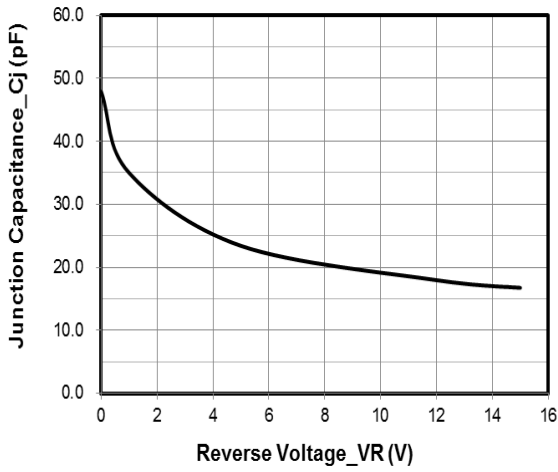
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	320	W
Peak Pulse Current (8/20 μs)	Ipp	10	A
ESD per IEC 61000-4-2 (Air)	VESD	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

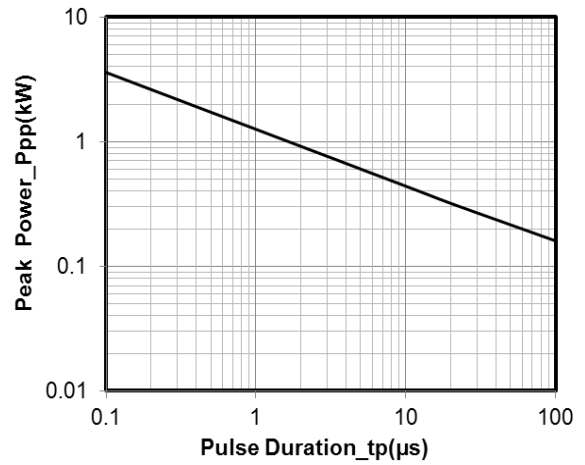
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			15	V	Pin 1 to Pin 2
Breakdown Voltage	VBR	16.5			V	IT = 1mA, Pin 1 to Pin 2
Reverse Leakage Current	IR			0.2	μA	VRWM = 15V, Pin 1 to Pin 2
Forward Voltage	VF			1.2	V	IF = 10mA, Pin 2 to Pin 1
Clamping Voltage	VC			21	V	IPP = 1A (8 x 20 μs pulse), Pin 1 to Pin 2
Clamping Voltage	VC			32	V	IPP = 10A (8 x 20 μs pulse), Pin 1 to Pin 2
Junction Capacitance	CJ		50		pF	VR = 0V, f = 1MHz

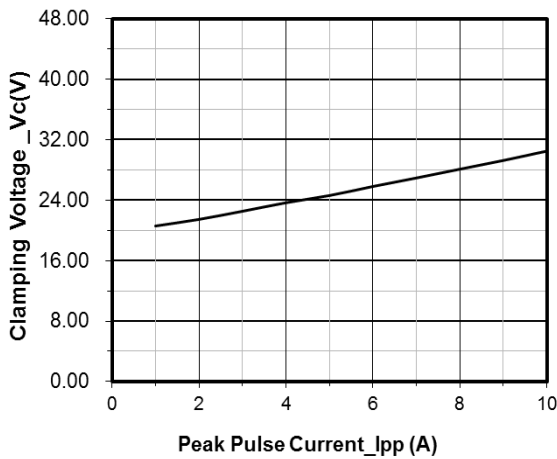
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)



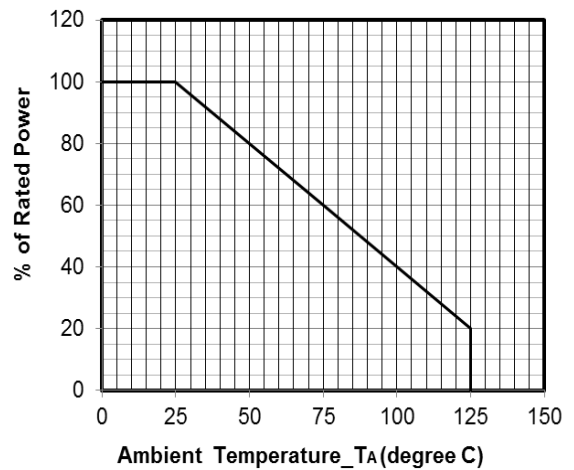
Junction Capacitance vs. Reverse Voltage



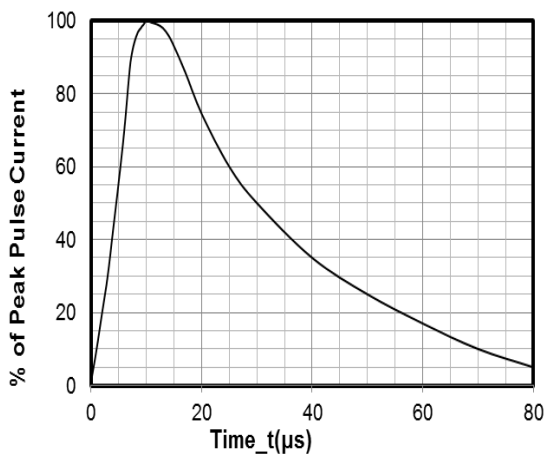
Peak Pulse Power vs. Pulse Time



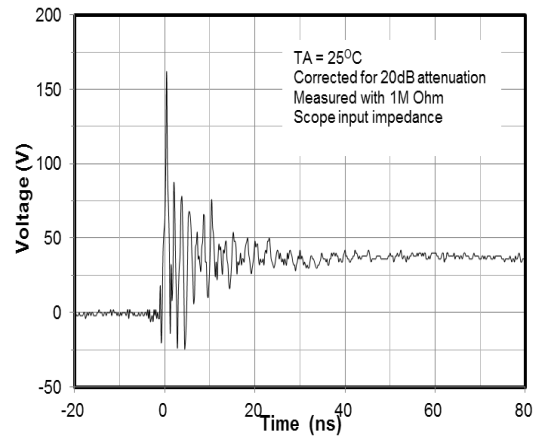
Clamping Voltage vs. Peak Pulse Current



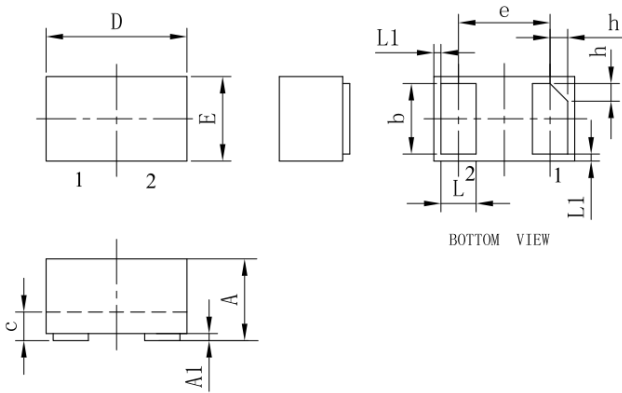
Power Derating Curve



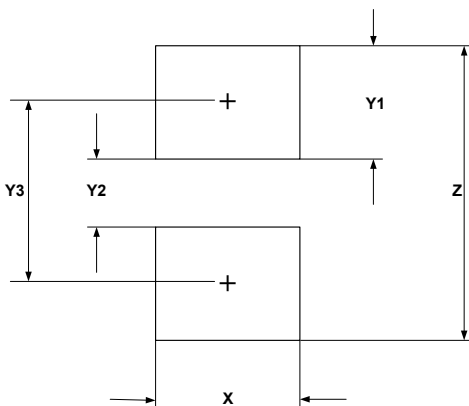
8 X 20 μs Pulse Waveform



ESD Clamping Voltage
8 kV Contact per IEC61000-4-2

DFN1006-2 Package Outline Drawing


SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.20	0.25	0.30	0.008	0.010	0.012
L1	0.05REF			0.002REF		
h	0.07	0.12	0.17	0.003	0.005	0.007

Suggested Land Pattern


SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052

Contact Information

Applied Power Microelectronics Co., Ltd.

 Website: <http://www.appliedpowermicro.com>

 Email: sales@appliedpowermicro.com

Phone: +86 (0519) 8399 3606